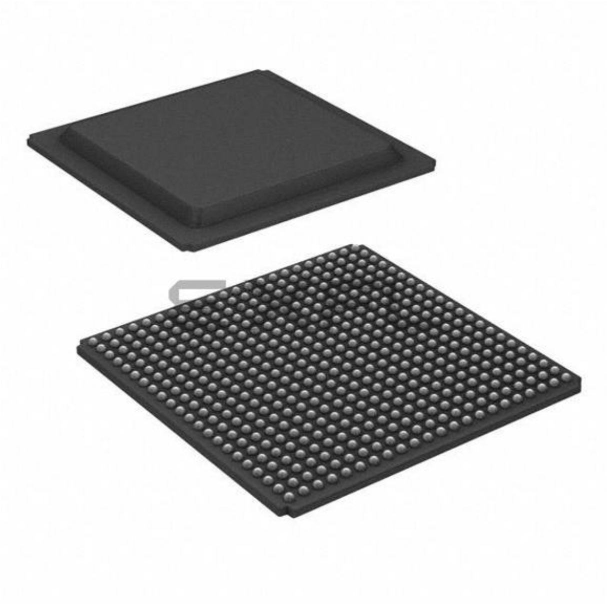

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	8000
Number of Logic Elements/Cells	102400
Total RAM Bits	4423680
Number of I/O	338
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7s100-1fgga484i

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{IN} [2][3][4]	I/O input voltage.	–0.4	V_{CCO} + 0.55	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33.[5]	–0.4	2.625	V
V_{CCBATT}	Key memory battery backup supply.	–0.5	2.0	V
XADC				
V_{CCADC}	XADC supply relative to GNDADC.	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC.	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies.[6]	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies.[6]	–	+260	°C
T_j	Maximum junction temperature.[6]	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. The maximum limit applies to DC signals. For maximum undershoot and overshoot AC specifications, see Table 4.
5. See Table 9 for TMDS_33 specifications.
6. For soldering guidelines and thermal considerations, see the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).	–	–	15	µA
C_{IN}[2]	Die input capacitance at the pad.	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	90	–	330	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	68	–	250	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	34	–	220	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	23	–	150	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	68	–	330	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state.	–	–	25	mA
I_{BATT}[3]	Battery supply current.	–	–	150	nA
R_{IN_TERM}[4]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40).	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50).	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60).	44	60	83	Ω
n	Temperature diode ideality factor.	–	1.010	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a V_{CCO}/2 level.

Table 5: **Typical Quiescent Supply Current[1][2][3]** ***(Cont'd)***

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
I_{CCOQ}	Quiescent V_{CCO} supply current.	XC7S6	1	1	1	1	1	1	mA
		XC7S15	1	1	1	1	1	1	mA
		XC7S25	1	1	1	1	1	1	mA
		XC7S50	1	1	1	1	1	1	mA
		XC7S75	4	4	4	4	4	4	mA
		XC7S100	4	4	4	4	4	4	mA
		XA7S6	N/A	1	N/A	1	1	N/A	mA
		XA7S15	N/A	1	N/A	1	1	N/A	mA
		XA7S25	N/A	1	N/A	1	1	N/A	mA
		XA7S50	N/A	1	N/A	1	1	N/A	mA
		XA7S75	N/A	4	N/A	4	4	N/A	mA
		XA7S100	N/A	4	N/A	4	4	N/A	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current.	XC7S6	10	10	10	10	10	10	mA
		XC7S15	10	10	10	10	10	10	mA
		XC7S25	13	13	13	13	13	13	mA
		XC7S50	22	22	22	22	22	20	mA
		XC7S75	43	43	43	43	43	43	mA
		XC7S100	43	43	43	43	43	43	mA
		XA7S6	N/A	10	N/A	10	10	N/A	mA
		XA7S15	N/A	10	N/A	10	10	N/A	mA
		XA7S25	N/A	13	N/A	13	13	N/A	mA
		XA7S50	N/A	22	N/A	22	22	N/A	mA
		XA7S75	N/A	43	N/A	43	43	N/A	mA
		XA7S100	N/A	43	N/A	43	43	N/A	mA

Table 5: **Typical Quiescent Supply Current[(1)(2)(3)] *(Cont'd)***

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XC7S6	1	1	1	1	1	1	mA
		XC7S15	1	1	1	1	1	1	mA
		XC7S25	1	1	1	1	1	1	mA
		XC7S50	2	2	2	2	2	1	mA
		XC7S75	9	9	9	9	9	8	mA
		XC7S100	9	9	9	9	9	8	mA
		XA7S6	N/A	1	N/A	1	1	N/A	mA
		XA7S15	N/A	1	N/A	1	1	N/A	mA
		XA7S25	N/A	1	N/A	1	1	N/A	mA
		XA7S50	N/A	2	N/A	2	2	N/A	mA
		XA7S75	N/A	9	N/A	9	9	N/A	mA
		XA7S100	N/A	9	N/A	9	9	N/A	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperature (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the *Xilinx Power Estimator* spreadsheet tool [Ref 6] to estimate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0 the following conditions apply.

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

There is no recommended sequence for supplies not discussed in this section.

Table 6 shows the minimum current, in addition to I_{CCQ} maximum, that is required by Spartan-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 are met, the device powers on after all four supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the *Xilinx Power Estimator* spreadsheet tool [Ref 6] to estimate current drain on these supplies.

Table 6: **Power-On Current**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
XC7S6	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S15	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S25	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S50	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S75	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S100	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S6	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S15	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S25	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S50	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S75	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S100	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA

Table 7: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}.		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}.		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}.		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}.		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$.	T_J = 125°C(1)	–	300	ms
		T_J = 100°C(1)	–	500	ms
		T_J = 85°C(1)	–	800	ms

Notes:

1. Based on 240,000 power cycles with a nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: **SelectIO DC Input and Output Levels**(1)(2)(3)

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.10	–0.10
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 6	Note 6
LVCMOS25	–0.300	0.7	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVCMOS33	–0.300	0.8	2.000	3.450	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVTTL	–0.300	0.8	2.000	3.450	0.400	2.400	Note 6	Note 6
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.10	–0.10
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.50	–0.50
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.00	–13.00
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.90	–8.90
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.00	–13.00
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.90	–8.90
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.00	–8.00
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.40	–13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in HR I/O banks.
3. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.

Table 9: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}(1)			V_{ID}(2)			V_{OCM}(3)			V_{OD}(4)		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	–	–	–	1.250	–	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	V_{CCO} – 0.405	V_{CCO} – 0.300	V_{CCO} – 0.190	0.400	0.600	0.800

Notes:
1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage ($Q - \overline{Q}$).
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage ($Q - \overline{Q}$).
5. V_{OD} for BLVDS will vary significantly depending on topology and loading.

Table 10: **Complementary Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}(1)			V_{ID}(2)		V_{OL}(3)	V_{OH}(4)	I_{OL}	I_{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO} – 0.400	8.00	–8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO} – 0.400	8.00	–8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	–	0.400	V_{CCO} – 0.400	16.00	–16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO} – 0.400	16.00	–16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.100	–0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	–	10% V_{CCO}	90% V_{CCO}	0.100	–0.100
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.00	–8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:
1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage ($Q - \overline{Q}$).
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

Table 17: **IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVTTL_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns
LVTTL_S8	1.34	1.41	1.41	3.66	3.92	3.92	3.69	3.93	3.93	ns
LVTTL_S12	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns
LVTTL_S16	1.34	1.41	1.41	3.19	3.45	3.45	3.22	3.46	3.46	ns
LVTTL_S24	1.34	1.41	1.41	3.41	3.67	3.67	3.44	3.68	3.68	ns
LVTTL_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns
LVTTL_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVTTL_F12	1.34	1.41	1.41	2.85	3.10	3.10	2.88	3.12	3.12	ns
LVTTL_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVTTL_F24	1.34	1.41	1.41	2.65	2.90	2.90	2.68	2.91	2.91	ns
LVDS_25	0.81	0.88	0.88	1.41	1.67	1.67	1.44	1.68	1.68	ns
MINI_LVDS_25	0.81	0.88	0.88	1.40	1.65	1.65	1.43	1.66	1.66	ns
BLVDS_25	0.81	0.88	0.88	1.96	2.21	2.21	1.99	2.23	2.23	ns
RSDS_25 (point to point)	0.81	0.88	0.88	1.40	1.65	1.65	1.43	1.66	1.66	ns
PPDS_25	0.81	0.88	0.88	1.41	1.67	1.67	1.44	1.68	1.68	ns
TMDS_33	0.81	0.88	0.88	1.54	1.79	1.79	1.57	1.80	1.80	ns
PCI33_3	1.32	1.39	1.39	3.22	3.48	3.48	3.25	3.49	3.49	ns
HSUL_12_S	0.75	0.82	0.82	1.93	2.18	2.18	1.96	2.20	2.20	ns
HSUL_12_F	0.75	0.82	0.82	1.41	1.67	1.67	1.44	1.68	1.68	ns
DIFF_HSUL_12_S	0.76	0.83	0.83	1.93	2.18	2.18	1.96	2.20	2.20	ns
DIFF_HSUL_12_F	0.76	0.83	0.83	1.41	1.67	1.67	1.44	1.68	1.68	ns
MOBILE_DDR_S	0.84	0.91	0.91	1.80	2.06	2.06	1.83	2.07	2.07	ns
MOBILE_DDR_F	0.84	0.91	0.91	1.51	1.76	1.76	1.54	1.77	1.77	ns
DIFF_MOBILE_DDR_S	0.78	0.85	0.85	1.82	2.07	2.07	1.85	2.09	2.09	ns
DIFF_MOBILE_DDR_F	0.78	0.85	0.85	1.57	1.82	1.82	1.60	1.84	1.84	ns
HSTL_I_S	0.75	0.82	0.82	1.74	1.99	1.99	1.77	2.01	2.01	ns
HSTL_II_S	0.73	0.80	0.80	1.54	1.79	1.79	1.57	1.80	1.80	ns
HSTL_I_18_S	0.75	0.82	0.82	1.41	1.67	1.67	1.44	1.68	1.68	ns
HSTL_II_18_S	0.75	0.81	0.81	1.54	1.79	1.79	1.57	1.80	1.80	ns
DIFF_HSTL_I_S	0.76	0.83	0.83	1.71	1.96	1.96	1.74	1.98	1.98	ns
DIFF_HSTL_II_S	0.76	0.83	0.83	1.63	1.88	1.88	1.66	1.90	1.90	ns
DIFF_HSTL_I_18_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns
DIFF_HSTL_II_18_S	0.78	0.85	0.85	1.58	1.84	1.84	1.61	1.85	1.85	ns
HSTL_I_F	0.75	0.82	0.82	1.22	1.48	1.48	1.25	1.49	1.49	ns
HSTL_II_F	0.73	0.80	0.80	1.24	1.49	1.49	1.27	1.51	1.51	ns
HSTL_I_18_F	0.75	0.82	0.82	1.26	1.51	1.51	1.29	1.52	1.52	ns

Table 17: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
HSTL_II_18_F	0.75	0.81	0.81	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_HSTL_I_F	0.76	0.83	0.83	1.30	1.56	1.56	1.33	1.57	1.57	ns
DIFF_HSTL_II_F	0.76	0.83	0.83	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_I_18_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_II_18_F	0.78	0.85	0.85	1.33	1.59	1.59	1.36	1.60	1.60	ns
LVCMOS33_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns
LVCMOS33_S8	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns
LVCMOS33_S12	1.34	1.41	1.41	3.21	3.46	3.46	3.24	3.48	3.48	ns
LVCMOS33_S16	1.34	1.41	1.41	3.52	3.77	3.77	3.55	3.79	3.79	ns
LVCMOS33_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns
LVCMOS33_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVCMOS33_F12	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVCMOS33_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVCMOS25_S4	1.20	1.27	1.27	3.26	3.51	3.51	3.29	3.52	3.52	ns
LVCMOS25_S8	1.20	1.27	1.27	3.01	3.26	3.26	3.04	3.27	3.27	ns
LVCMOS25_S12	1.20	1.27	1.27	2.60	2.85	2.85	2.63	2.87	2.87	ns
LVCMOS25_S16	1.20	1.27	1.27	2.94	3.20	3.20	2.97	3.21	3.21	ns
LVCMOS25_F4	1.20	1.27	1.27	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVCMOS25_F8	1.20	1.27	1.27	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS25_F12	1.20	1.27	1.27	2.29	2.54	2.54	2.32	2.55	2.55	ns
LVCMOS25_F16	1.20	1.27	1.27	2.13	2.39	2.39	2.16	2.40	2.40	ns
LVCMOS18_S4	0.83	0.89	0.89	1.74	1.99	1.99	1.77	2.01	2.01	ns
LVCMOS18_S8	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS18_S12	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS18_S16	0.83	0.89	0.89	1.65	1.90	1.90	1.68	1.91	1.91	ns
LVCMOS18_S24	0.83	0.89	0.89	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVCMOS18_F4	0.83	0.89	0.89	1.57	1.82	1.82	1.60	1.84	1.84	ns
LVCMOS18_F8	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVCMOS18_F12	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVCMOS18_F16	0.83	0.89	0.89	1.52	1.77	1.77	1.55	1.79	1.79	ns
LVCMOS18_F24	0.83	0.89	0.89	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVCMOS15_S4	0.86	0.93	0.93	2.18	2.43	2.43	2.21	2.45	2.45	ns
LVCMOS15_S8	0.86	0.93	0.93	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVCMOS15_S12	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVCMOS15_S16	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVCMOS15_F4	0.86	0.93	0.93	1.97	2.23	2.23	2.00	2.24	2.24	ns

Table 18: **IOB 3-state Output Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{IOTPHZ}	T input to pad high-impedance.	2.19	2.37	2.37	ns
$T_{IOIBUFDISABLE}$	IBUF turn-on time from IBUFDISABLE to O output.	2.30	2.60	2.60	ns

Table 19: **Input Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	V_L[(1)]	V_H[(1)]	V_{MEAS}[(3)(5)]	V_{REF}[(2)(4)]
PPDS_25	PPDS_25	1.25 – 0.125	1.25 + 0.125	0[(5)]	–
RSDS_25	RSDS_25	1.25 – 0.125	1.25 + 0.125	0[(5)]	–
TMDS_33	TMDS_33	3 – 0.125	3 + 0.125	0[(5)]	–

Notes:

1. Input waveform switches between V_L and V_H.
2. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
3. Input voltage level from which measurement starts.
4. This is an input voltage reference that bears no relation to the V_{REF} / V_{MEAS} parameters found in IBIS models and/or noted in Figure 1.
5. The value given is the differential input voltage.

Table 20: **Output Delay Measurement Methodology**

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}[1] (pF)	V_{MEAS} (V)	V_{REF} (V)
LVCMOS, 1.2V	LVCMOS12	1M	0	0.6	0
LVCMOS, 1.5V	LVCMOS15	1M	0	0.75	0
LVCMOS, 1.8V	LVCMOS18	1M	0	0.9	0
LVCMOS, 2.5V	LVCMOS25	1M	0	1.25	0
LVCMOS, 3.3V	LVCMOS33	1M	0	1.65	0
LVTTL, 3.3V	LVTTL	1M	0	1.65	0
PCI33, 3.3V	PCI33_3	25	10	1.65	0
HSTL (high-speed transceiver logic), Class I, 1.2V	HSTL_I_12	50	0	V_{REF}	0.6
HSTL, Class I, 1.5V	HSTL_I	50	0	V_{REF}	0.75
HSTL, Class II, 1.5V	HSTL_II	25	0	V_{REF}	0.75
HSTL, Class I, 1.8V	HSTL_I_18	50	0	V_{REF}	0.9
HSTL, Class II, 1.8V	HSTL_II_18	25	0	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	50	0	V_{REF}	0.6
SSTL12, 1.2V	SSTL12	50	0	V_{REF}	0.6
SSTL135/SSTL135_R, 1.35V	SSTL135, SSTL135_R	50	0	V_{REF}	0.675
SSTL15/SSTL15_R, 1.5V	SSTL15, SSTL15_R	50	0	V_{REF}	0.75
SSTL (stub-series terminated logic), Class I & Class II, 1.8V	SSTL18_I, SSTL18_II	50	0	V_{REF}	0.9
DIFF_MOBILE_DDR, 1.8V	DIFF_MOBILE_DDR	50	0	V_{REF}	0.9
DIFF_HSTL, Class I, 1.2V	DIFF_HSTL_I_12	50	0	V_{REF}	0.6
DIFF_HSTL, Class I & II, 1.5V	DIFF_HSTL_I, DIFF_HSTL_II	50	0	V_{REF}	0.75
DIFF_HSTL, Class I & II, 1.8V	DIFF_HSTL_I_18, DIFF_HSTL_II_18	50	0	V_{REF}	0.9
DIFF_HSUL_12, 1.2V	DIFF_HSUL_12	50	0	V_{REF}	0.6
DIFF_SSTL135/DIFF_SSTL135_R, 1.35V	DIFF_SSTL135, DIFF_SSTL135_R	50	0	V_{REF}	0.675
DIFF_SSTL15/DIFF_SSTL15_R, 1.5V	DIFF_SSTL15, DIFF_SSTL15_R	50	0	V_{REF}	0.75
DIFF_SSTL18, Class I & II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	50	0	V_{REF}	0.9
LVDS, 2.5V	LVDS_25	100	0	0[2]	0
BLVDS (Bus LVDS), 2.5V	BLVDS_25	100	0	0[2]	0
Mini LVDS, 2.5V	MINI_LVDS_25	100	0	0[2]	0
PPDS_25	PPDS_25	100	0	0[2]	0
RSDS_25	RSDS_25	100	0	0[2]	0
TMDS_33	TMDS_33	50	0	0[2]	3.3

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

Input Serializer/Deserializer Switching Characteristics

Table 23: **ISERDES Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold for Control Lines					
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin setup/hold with respect to CLKDIV.	0.02/0.15	0.02/0.17	0.02/0.17	ns
T_{ISCCK_CE}/ T_{ISCKC_CE}	CE pin setup/hold with respect to CLK (for CE1).	0.50/–0.01	0.72/–0.01	0.72/–0.01	ns
T_{ISCCK_CE2}/ T_{ISCKC_CE2}	CE pin setup/hold with respect to CLKDIV (for CE2).	–0.10/0.36	–0.10/0.40	–0.10/0.40	ns
Setup/Hold for Data Lines					
T_{ISDCK_D}/ T_{ISCKD_D}	D pin setup/hold with respect to CLK.	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
T_{ISDCK_DDLY}/ T_{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY).(1)	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
$T_{ISDCK\_D\_DDR}$/ $T_{ISCKD\_D\_DDR}$	D pin setup/hold with respect to CLK at DDR mode.	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin setup/hold with respect to CLK at DDR mode (using IDELAY).(1)	0.14/0.14	0.17/0.17	0.17/0.17	ns
Sequential Delays					
T_{ISCKO_Q}	CLKDIV to out at Q pin.	0.54	0.66	0.66	ns
Propagation Delays					
T_{ISDO_DO}	D input to DO output pin.	0.11	0.13	0.13	ns

Notes:

1. Recorded at 0 tap value.

Table 26: **IO_FIFO Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
IO_FIFO Clock to Out Delays					
T_{OFFCKO_DO}	RDCLK to Q outputs.	0.60	0.68	0.68	ns
T_{CKO_FLAGS}	Clock to IO_FIFO flags.	0.61	0.77	0.77	ns
Setup/Hold					
T_{CCK_D}/T_{CKC_D}	D inputs to WRCLK.	0.51/0.02	0.58/0.02	0.58/0.02	ns
$T_{IFFCCK\_WREN}/$ T_{IFFCKC_WREN}	WREN to WRCLK.	0.47/–0.01	0.53/–0.01	0.53/–0.01	ns
$T_{OFFCCK\_RDEN}/$ T_{OFFCKC_RDEN}	RDEN to RDCLK.	0.58/0.02	0.66/0.02	0.66/0.02	ns
Minimum Pulse Width					
$T_{PWH\_IO\_FIFO}$	RESET, RDCLK, WRCLK.	2.15	2.15	2.15	ns
$T_{PWL\_IO\_FIFO}$	RESET, RDCLK, WRCLK.	2.15	2.15	2.15	ns
Maximum Frequency					
F_{MAX}	RDCLK and WRCLK.	200.00	200.00	200.00	MHz

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 28: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Sequential Delays					
T_{SHCKO}	Clock to A – B outputs.	1.09	1.32	1.32	ns, Max
T_{SHCKO_1}	Clock to AMUX – BMUX outputs.	1.53	1.86	1.86	ns, Max
Setup and Hold Times Before/After Clock CLK					
T_{DS_LRAM}/T_{DH_LRAM}	A – D inputs to CLK.	0.60/0.30	0.72/0.35	0.72/0.35	ns, Min
T_{AS_LRAM}/T_{AH_LRAM}	Address An inputs to clock.	0.30/0.60	0.37/0.70	0.37/0.70	ns, Min
	Address An inputs through MUXs and/or carry logic to clock.	0.77/0.21	0.94/0.26	0.94/0.26	ns, Min
T_{WS_LRAM}/T_{WH_LRAM}	WE input to clock.	0.43/0.12	0.53/0.17	0.53/0.17	ns, Min
$T_{CECK\_LRAM}/T_{CKCE\_LRAM}$	CE input to CLK.	0.44/0.11	0.53/0.17	0.53/0.17	ns, Min
Clock CLK					
T_{MPW_LRAM}	Minimum pulse width.	1.13	1.25	1.25	ns, Min
T_{MCP}	Minimum clock period.	2.26	2.50	2.50	ns, Min

Notes:

1. T_{SHCKO} also represents the CLK to XMUX output. Refer to the timing report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 29: **CLB Shift Register Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Sequential Delays					
T_{REG}	Clock to A – D outputs.	1.33	1.61	1.61	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output.	1.77	2.15	2.15	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output.	1.23	1.46	1.46	ns, Max
Setup and Hold Times Before/After Clock CLK					
$T_{WS\_SHFREG}/ T_{WH\_SHFREG}$	WE input.	0.41/0.12	0.51/0.17	0.51/0.17	ns, Min
$T_{CECK\_SHFREG}/ T_{CKCE\_SHFREG}$	CE input to CLK.	0.42/0.11	0.52/0.17	0.52/0.17	ns, Min
$T_{DS\_SHFREG}/ T_{DH\_SHFREG}$	A – D inputs to CLK.	0.37/0.37	0.44/0.43	0.44/0.43	ns, Min
Clock CLK					
T_{MPW_SHFREG}	Minimum pulse width.	0.86	0.98	0.98	ns, Min

Table 30: **Block RAM and FIFO Switching Characteristics *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$F_{MAX\_CAS\_RF\_DELAYED\_WRITE}$	When in cascade RF mode and there is a possibility of address overlap between port A and port B.	362.19	297.35	297.35	MHz
F_{MAX_FIFO}	FIFO in all modes without ECC.	460.83	388.20	388.20	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration.	365.10	297.53	297.53	MHz

Notes:

1. T_{RCKO_DOR} includes T_{RCKO_DOW}, T_{RCKO_DOPR}, and T_{RCKO_DOPW} as well as the B port equivalent timing parameters.
2. These parameters also apply to synchronous FIFO with DO_REG = 0.
3. T_{RCKO_DO} includes T_{RCKO_DOP} as well as the B port equivalent timing parameters.
4. These parameters also apply to multi-rate (asynchronous) and synchronous FIFO with DO_REG = 1.
5. T_{RCKO_FLAGS} includes the following parameters: T_{RCKO_AEMPTY}, T_{RCKO_AFULL}, T_{RCKO_EMPTY}, T_{RCKO_FULL}, T_{RCKO_RDERR}, T_{RCKO_WRERR}.
6. $T_{RCKO\_POINTERS}$ includes both $T_{RCKO\_RDCOUNT}$ and $T_{RCKO\_WRCOUNT}$.
7. The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
8. These parameters include both A and B inputs as well as the parity inputs of A and B.
9. T_{RCO_FLAGS} includes the following flags: AEMPTY, AFULL, EMPTY, FULL, RDERR, WRERR, RDCOUNT, and WRCOUNT.
10. RDEN and WREN must be held Low prior to and during reset. The FIFO reset must be asserted for at least five positive clock edges of the slowest clock (WRCLK or RDCLK).

Table 35: **Horizontal Clock Buffer Switching Characteristics (BUFH)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{BHCKO_O}	BUFH delay from I to O.	0.11	0.13	0.13	ns
T_{BHCCK_CE}/ T_{BHCKC_CE}	CE pin setup and hold.	0.22/0.15	0.28/0.21	0.28/0.21	ns
Maximum Frequency					
F_{MAX_BUFH}	Horizontal clock buffer (BUFH).	628.00	464.00	464.00	MHz

Table 36: **Duty Cycle Distortion and Clock-Tree Skew**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
T_{DCD_CLK}	Global clock tree duty-cycle distortion.[1]	All	0.20	0.20	0.20	ns
T_{CKSKEW}	Global clock tree skew.[2]	XC7S6	0.05	0.06	0.06	ns
		XC7S15	0.05	0.06	0.06	ns
		XC7S25	0.26	0.26	0.26	ns
		XC7S50	0.26	0.26	0.26	ns
		XC7S75	0.33	0.36	0.36	ns
		XC7S100	0.33	0.36	0.36	ns
		XA7S6	0.05	0.06	N/A	ns
		XA7S15	0.05	0.06	N/A	ns
		XA7S25	0.26	0.26	N/A	ns
		XA7S50	0.26	0.26	N/A	ns
		XA7S75	0.33	0.36	N/A	ns
		XA7S100	0.33	0.36	N/A	ns
T_{DCD_BUFIO}	I/O clock tree duty cycle distortion.	All	0.14	0.14	0.14	ns
$T_{BUFIOSKEW}$	I/O clock tree skew across one clock region.	All	0.03	0.03	0.03	ns
T_{DCD_BUFR}	Regional clock tree duty cycle distortion.	All	0.18	0.18	0.18	ns

Notes:

1. These parameters represent the worst-case duty cycle distortion observable at the I/O flip flops. For all I/O standards, IBIS can be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times.
2. The T_{CKSKEW} value represents the worst-case clock-tree skew observable between sequential I/O elements. Significantly less clock-tree skew exists for I/O registers that are close to each other and fed by the same or adjacent clock-tree branches. Use the Xilinx timing analysis tools to evaluate clock skew specific to your application.

Table 38: **PLL Specification**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$PLL\_F_{BANDWIDTH}$	Low PLL bandwidth at typical.	1.00	1.00	1.00	MHz
	High PLL bandwidth at typical.(1)	4.00	4.00	4.00	MHz
$PLL\_T_{STATPHAOFFSET}$	Static phase offset of the PLL outputs.(2)	0.12	0.12	0.12	ns
$PLL\_T_{OUTJITTER}$	PLL output jitter.	Note 3			
$PLL\_T_{OUTDUTY}$	PLL output clock duty-cycle precision.(4)	0.20	0.20	0.20	ns
$PLL\_T_{LOCKMAX}$	PLL maximum lock time.	100.00	100.00	100.00	µs
PLL_F_{OUTMAX}	PLL maximum output frequency.	800.00	800.00	800.00	MHz
PLL_F_{OUTMIN}	PLL minimum output frequency.(5)	6.25	6.25	6.25	MHz
$PLL\_T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max			
$PLL\_RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	ns
PLL_F_{PFDMAX}	Maximum frequency at the phase frequency detector.	500.00	450.00	450.00	MHz
PLL_F_{PFDMIN}	Minimum frequency at the phase frequency detector.	19.00	19.00	19.00	MHz
$PLL\_T_{FBDELAY}$	Maximum delay in the feedback path.	3 ns Max or one CLKIN cycle			
Dynamic Reconfiguration Port (DRP) for PLL Before and After DCLK					
T_{PLLDCK_DADDR}/ T_{PLLCKD_DADDR}	Setup and hold of D address.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
T_{PLLDCK_DI}/ T_{PLLCKD_DI}	Setup and hold of D input.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
T_{PLLDCK_DEN}/ T_{PLLCKD_DEN}	Setup and hold of D enable.	1.97/0.00	2.29/0.00	2.29/0.00	ns, Min
T_{PLLDCK_DWE}/ T_{PLLCKD_DWE}	Setup and hold of D write enable.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
T_{PLLCKO_DRDY}	CLK to out of DRDY.	0.72	0.99	0.99	ns, Max
F_{DCK}	DCLK frequency.	200.00	200.00	200.00	MHz, Max

Notes:

1. The PLL does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any PLL outputs with identical phase.
3. Values for this parameter are available in the *Clocking Wizard* [Ref 8].
4. Includes global clock buffer.
5. Calculated as FVCO/128 assuming output duty cycle is 50%.

Table 45: **Clock-Capable Clock Input Setup and Hold With MMCM**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for SSTL15 Standard.[1][2]						
$T_{PSMMCMCC}$/ $T_{PHMMCMCC}$	No delay clock-capable clock input and IFF[3] with MMCM.	XC7S6	2.73/–0.59	3.27/–0.59	3.27/–0.59	ns
		XC7S15	2.73/–0.59	3.27/–0.59	3.27/–0.59	ns
		XC7S25	2.69/–0.61	3.21/–0.61	3.21/–0.61	ns
		XC7S50	2.81/–0.62	3.35/–0.62	3.35/–0.62	ns
		XC7S75	2.81/–0.62	3.36/–0.62	3.36/–0.62	ns
		XC7S100	2.81/–0.62	3.36/–0.62	3.36/–0.62	ns
		XA7S6	2.73/–0.59	3.27/–0.59	N/A	ns
		XA7S15	2.73/–0.59	3.27/–0.59	N/A	ns
		XA7S25	2.69/–0.61	3.21/–0.61	N/A	ns
		XA7S50	2.81/–0.62	3.35/–0.62	N/A	ns
		XA7S75	2.81/–0.62	3.36/–0.62	N/A	ns
		XA7S100	2.81/–0.62	3.36/–0.62	N/A	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. Use IBIS to determine any duty-cycle distortion incurred using various standards.
3. IFF = Input flip-flop or latch.

Table 48: **Sample Window**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{SAMP}	Sampling error at receiver pins.(1)	0.64	0.70	0.70	ns
T_{SAMP_BUFIO}	Sampling error at receiver pins using BUFIO.(2)	0.40	0.46	0.46	ns

Notes:

1. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
   - CLK0 MMCM jitter
   - MMCM accuracy (phase offset)
   - MMCM phase shift resolution

   These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IDELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.